

Akihiro Suzuki

List of Publications by Year in descending order

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Version: 2024-02-01

10
papers

43
citations

1937685

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1872680

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all docs

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docs citations

10
times ranked

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citing authors

#	ARTICLE	IF	CITATIONS
1	Hydrogen diffusion behavior in CH ₂ P-molecular-ion-implanted silicon wafers for CMOS image sensors. <i>Materials Science in Semiconductor Processing</i> , 2022, 137, 106211.	4.0	1
2	In Situ Transmission Electron Microscopy Study of Shrinkage Kinetics of CH ₄ -Molecular-Ion-Implantation-Induced Extended Defects. <i>Journal of the Electrochemical Society</i> , 2022, 169, 047521.	2.9	1
3	Proximity gettering design of silicon wafers using silicon hydride and hydrocarbon mixture molecular ion implantation technique. <i>Materials Science in Semiconductor Processing</i> , 2021, 135, 106063.	4.0	3
4	Reduction of Dark Current in CMOS Image Sensor Pixels Using Hydrocarbon-Molecular-Ion-Implanted Double Epitaxial Si Wafers. <i>Sensors</i> , 2020, 20, 6620.	3.8	9
5	Influence of oxygen on copper gettering in hydrocarbon molecular ion implanted region using atom probe tomography. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2020, 478, 99-103.	1.4	4
6	Hydrogen passivation for reduction of SiO ₂ /Si interface state density using hydrocarbon-molecular-ion-implanted silicon wafers. <i>Japanese Journal of Applied Physics</i> , 2020, 59, 125502.	1.5	13
7	Photoemission Spectroscopy Study on Hydrogen Termination Effect on SiO ₂ /Si Structure Fabricated Using H ⁺ -Implanted Si Substrate. <i>Journal of the Electrochemical Society</i> , 2020, 167, 127505.	2.9	1
8	Molecular and Atomic Hydrogen Diffusion Behavior by Reaction Kinetic Analysis in Projection Range of Hydrocarbon Molecular Ion for CMOS Image Sensors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900175.	1.8	5
9	Fundamental Characteristics of Cyanide-Related Multielement Molecular Ion-Implanted Epitaxial Si Wafers for High-Performance CMOS Image Sensors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900172.	1.8	5
10	Effect of ramping up rate on end of range defect in multielement molecular-ion (CH ₃ O)-implanted silicon wafers. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 121002.	1.5	1